

Supplementary materials

Enhancement in Photoelectrochemical Performance of Optimized Amorphous SnS₂ Thin Film Fabricated Through Atomic Layer Deposition

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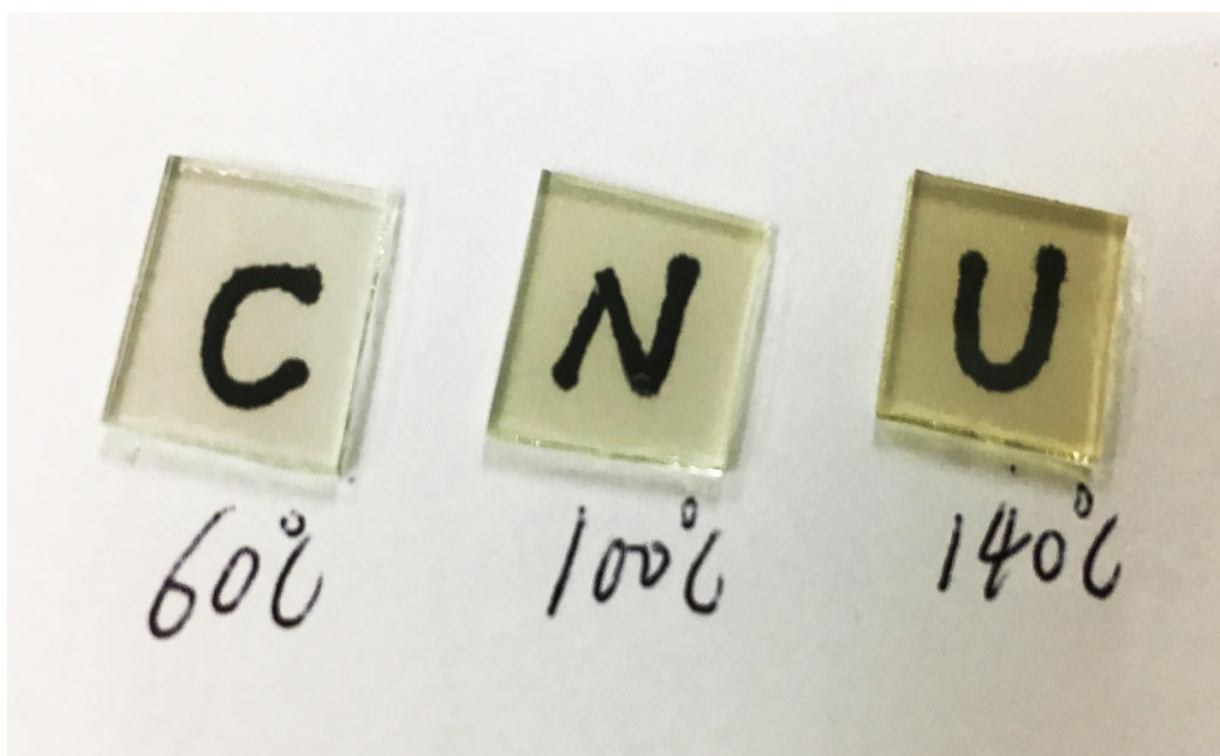


Figure S1. Photos of 50-nm-thick SnS₂ films which in the growth of the glass substrates at different deposition temperatures. The C, N, and U represent the deposition temperature of 60, 100, and 140 °C, respectively. All of them are pale yellow and the color deepens with the increase of deposition temperature.

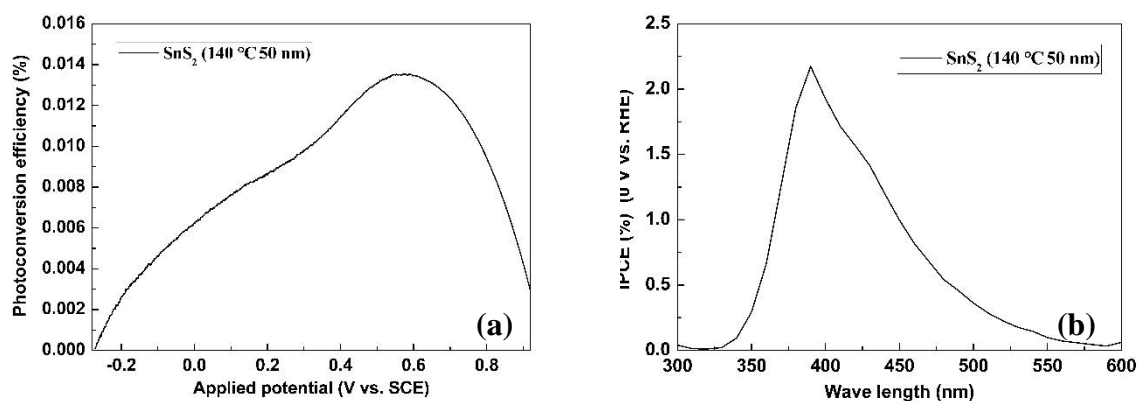


Figure S2. Photoconversion efficiency **(a)** and IPCE curve **(b)** of the 50-nm-thick SnS₂ film deposited at 140 °C. Photoconversion efficiency was measured as a function of applied potential (vs. SCE) under illumination. The maximum efficiency (0.014%) was identified at ~0.553 V of bias (vs. SCE). The highest IPCE value was up to 2.17% at 390 nm (0 V vs. RHE).



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